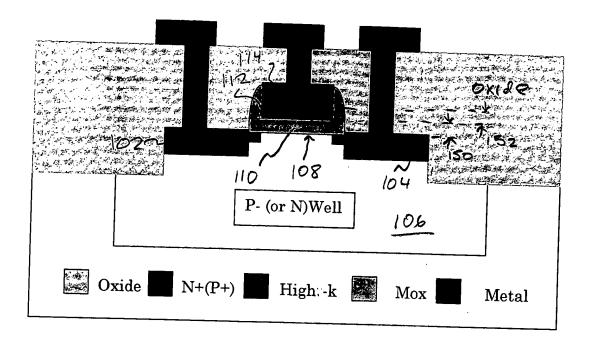
100



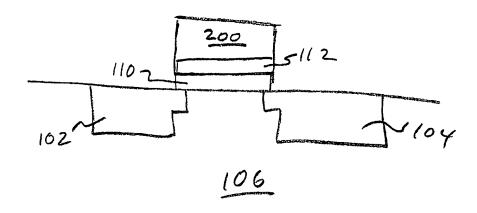


Fig. 2

100 K

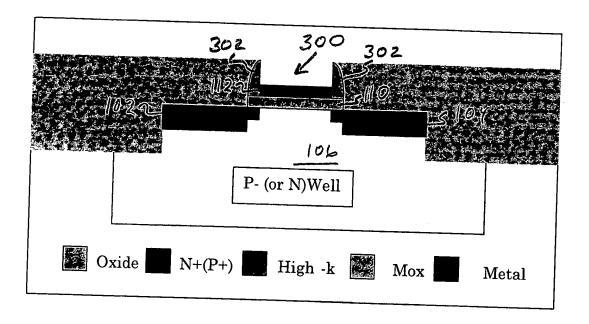


Fig. 3

BEST AVAILABLE COPY

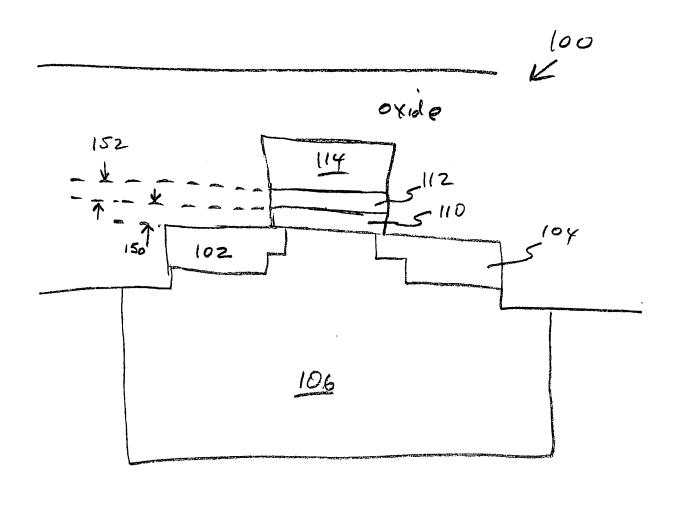


Fig. 4

100

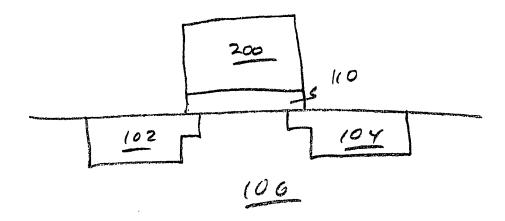


Fig. 5

(00 K

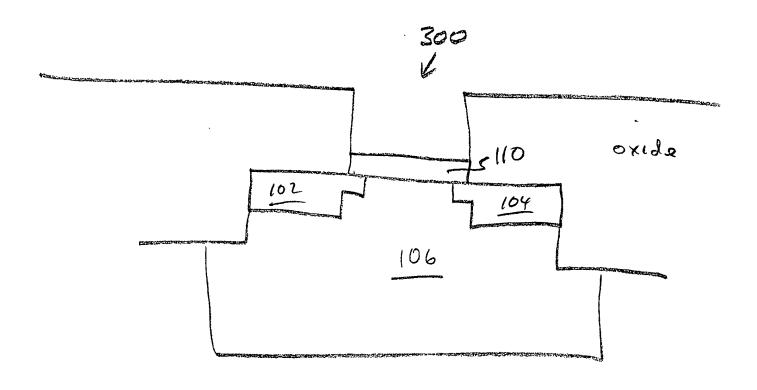


Fig. 6

START Source and drain Megions torming depositing Surface channe high-le dielectric depositing placeholder 1600 processing 5709 depositing etching placeholder torming gate electrode sidewall insulaheavy ion implanting

Fig. 7

START JU 800 Source and Stain regions Jorming 400 Processing L5803a heavy 100 implanting positing tace channel depositing placeholder materia Lepositing placeholder torming

Fig. 8